

TIP132 TIP135 TIP137

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

 STMicroelectronics PREFERRED SALESTYPES

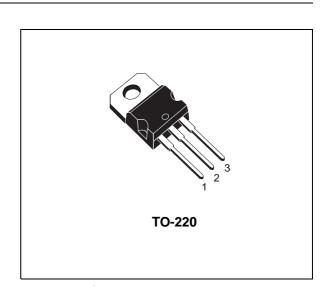
APPLICATION

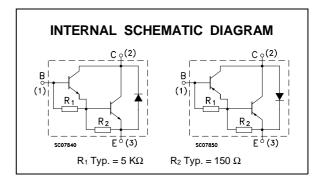
 LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The TIP132 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration, mounted in Jedec TO-220 plastic package. It is intented for use in power linear and switching applications.

The complementary PNP type is TIP137 . Also TIP135 is a PNP type.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Val	Unit	
		NPN		TIP132	
		PNP	TIP135	TIP137	
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	Base Voltage (I _C = 0)		5	
Ic	Collector Current		8	А	
Ісм	Collector Peak Current		12		Α
I _B	Base Current		0.	Α	
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C		70		W
	T _{amb} ≤ 25 °C		2		W
T _{stg}	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		150		°C

^{*} For PNP types voltage and current values are negative.

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TIP132 / TIP135 / TIP137

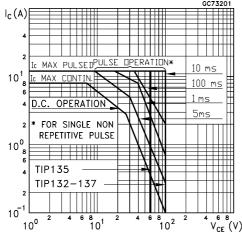
THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	63.5	°C/W

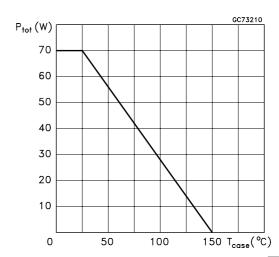
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = Half Rated V	CEO			0.5	mA
I _{CBO}	Collector Cut-off Current (I _E = 0)	V_{CB} = Rated V_{CBO}				0.2	mA
I _{EBO}	Emitter Cut-off Current (Ic = 0)	V _{EB} = 5 V				5	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP135 for TIP132/TIP137		60 100			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 4 A I _C = 6 A	$I_B = 16 \text{ mA}$ $I_B = 30 \text{ mA}$			2 4	V V
V _{BE} *	Base-Emitter Voltage	I _C = 4 A	V _{CE} = 4 V			2.5	V
h _{FE} *	DC Current Gain	I _C = 1 A I _C = 4 A	V _{CE} = 4 V V _{CE} = 4 V	500 1000		15000	

Safe Operating Areas



Power Derating Curve

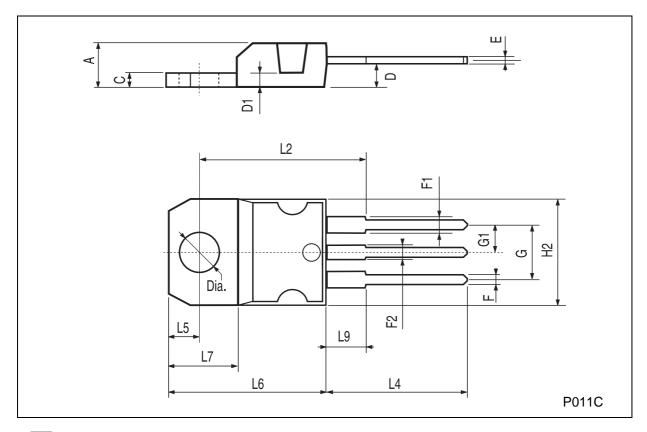


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^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
Е	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



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